

The paragraph beginning at page 6, line 8 has been changed as follows:

A2 Referring to Fig 4B, the hard mask layer 5 is patterned by an etch process using the photolithographic film patterns 6 as a mask to form hard masks 5a.

The paragraph beginning at page 6, line 11 has been changed as follows:

AB By reference to Fig. 4C, the metal layer 4, the polysilicon layer 3 and the gate oxide film 2 are sequentially patterned by an etch process using the hard masks 5a as a mask to form a gate electrode 4a. Next, an impurity ion is implanted into the semiconductor substrate 1 at both sides of the gate electrode 4a to form a junction region 7.

The paragraph beginning at page 6, line 16 has been changed as follows:

Ad Referring now to Fig. 4D, a spacer 8 as an insulating film is formed at both sides of the hard mask 5a and the gate electrode 4a. The insulating film for forming the spacer 8 may be formed using a nitride film such as the nitride film used as the hard mask 5a. At this time, the nitride film is formed by a low-pressure chemical vapor deposition (LPCVD) method in a batch type chamber having the pressure of below 1 Torr, preferably 0.1 Torr to 1 Torr. The thickness of the nitride film is 50Å to 1000Å.

IN THE DRAWINGS:

Please enter the following change to the drawing:

Please label Figs. 1A-1D and Fig. 3 with the legend "Prior Art", and add new Figs. 4A-4D.

A request for approval of drawings changes is submitted herewith.